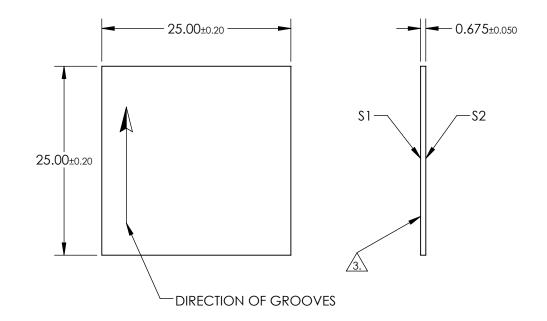
NOTES:

- SUBSTRATE MATERIAL: Single Crystal Silicon
- PERIOD: 855 ±42.75nm 2. LINE WIDTH: 425 ±42.5nm GROOVE DEPTH: 200 ±30nm

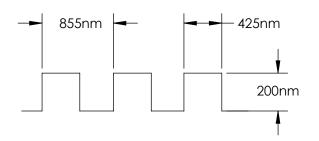


RIE TREATED SURFACE

4. **ROHS COMPLIANT**



CROSS SECTION VIEW OF GRATING SURFACE



PARTS TO THIS DRAWING

SPECIFICATIONS SUBJECT TO CHANGE WITHOUT NOTICE DIMENSIONS ARE FOR REFERENCE ONLY

SHEET

1 OF 1

	S1	S2
SHAPE	PLANO	PLANO
SURFACE QUALITY	60-40 (within CA)	FINE GRIND
CLEAR APERTURE	24.00 x 24.00	N/A
BEVEL	PROTECTED AS NEEDED	PROTECTED AS NEEDED

			Edmund Option	S®
THIRD ANGLE PROJECTION		TITLE	II-VI LightSmyth™ 855nm, 200nm Grod Depth, 25mm Sq. Linear Silicon Nanost	
ALL DIMS IN	mm	DWG NO	16856	SHEET 1 OF